

FORM PTO-1449  
(Rev. 5/92)O'SHEA GETZ P.C.  
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APPLICANT: Burgmair et al.

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EXAMINER: Diana C. Garrity

**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	H	JP 08189870	7/23/1996	Japan	9	12	Yes-Abstract
	I	JP 56100350	8/12/1981	Japan	27	30	Yes-Abstract
	J	JP 63171355	7/15/1988	Japan	27	30	Yes-Abstract
	K						

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	L	Matsushima Toshinori et al., "Organic-inorganic field effect transistor with SnI <sub>2</sub> -based perovskite channel layer using vapour phase deposition technique," Proceedings of the SPIE-The International Society for Optical Engineering, 2003, Vol. 5217, Pages 43-54 (ABSTRACT) CAPLUS [online]
	M	Sudholter, Ernst et al., "Modification of ISFETs by covalent anchoring of poly(hydroxyethylmethacrylate)hydrogel. Introduction of thermodynamically defined semiconductor-sensing membrane interface." Analytica Chimica Acta, 1990, Vol. 230, No. 1, Pages 59-65 (ABSTRACT) CAPLUS [online]
	N	
	O	
	P	
	Q	

EXAMINER

DATE CONSIDERED

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Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.